

## ACPL-337J

### 4.0A Gate Drive Optocoupler with Integrated (VCE) Desaturation Detection, Active Miller Clamping, Fault and UVLO Status Feedback

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#### Overview

The Broadcom<sup>®</sup> ACPL-337J gate drive optocoupler features fast propagation delay with excellent timing skew performance. Smart features that are integrated to protect the IGBT include IGBT desaturation detection with soft-shutdown protection and fault feedback, undervoltage lockout and feedback, and active Miller current clamping. This full-featured and easy-to-implement IGBT gate drive optocoupler comes in a compact, surface-mountable SO-16 package for space savings. It is suitable for driving IGBTs and power MOSFETs used in motor control and inverter applications.

Broadcom isolation products provide reinforced insulation and reliability that delivers safe signal isolation critical in high voltage and noisy industrial applications.

#### Applications

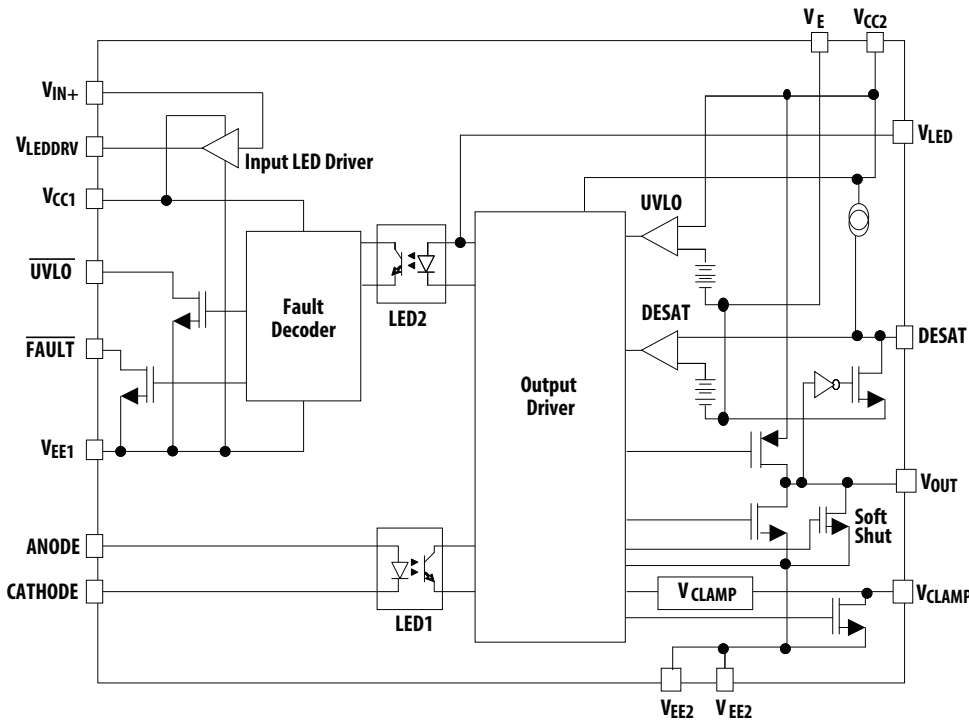
- Isolated IGBT/Power MOSFET gate drive
- Renewable energy inverters
- AC and brushless DC motor drives
- Industrial inverters
- Switching power supplies

#### Features

- 4.0A maximum peak output current
- Rail-to-rail output voltage
- 3.0A Miller clamp
- IGBT desaturation detection
- Integrated fail-safe IGBT protection
  - Desaturation detection, *soft* IGBT turn-off and fault feedback
  - Undervoltage lockout (UVLO) Protection with feedback
- 250-ns maximum propagation delay over temperature
- Integrated LED driver
- 30-kV/ $\mu$ s minimum common mode rejection (CMR) at  $V_{CM} = 1500V$
- Wide operating voltage: 15V to 30V
- Wide operating temperature range:  $-40^{\circ}C$  to  $105^{\circ}C$
- SO-16 package with 8-mm clearance and creepage
- Regulatory approvals
  - UL 1577,  $V_{ISO} = 5000 V_{RMS}$  for 1 minute
  - CSA
  - IEC/EN/DIN-EN 60747-5-5  $V_{IORM} = 1414 V_{PEAK}$

**CAUTION!** Take normal static precautions in the handling and assembly of this component to prevent damage and degradation that might be induced by electrostatic discharge (ESD). The components featured in this data sheet are not recommended to be used in military or aerospace applications or environments.

# Functional Diagram



## Product Overview Description

The ACPL-337J is a highly integrated power control device that incorporates all the necessary components for a complete, isolated IGBT gate drive circuit. It features IGBT desaturation detection with soft-shutdown protection and fault feedback, undervoltage lockout and feedback, and active Miller current clamping in a SO-16 package. Direct LED input with or without integrated LED driver allows flexible logic configuration and differential current mode driving with low input impedance, greatly increasing its noise immunity.

## Pin Description



Pin	Symbol	Description
1	$V_{EE1}$	Input common.
2	$V_{IN+}$	Noninverting voltage control input.
3	$V_{CC1}$	Input power supply (4.5V to 5.5V).
4	$V_{LEDDRV}$	Integrated LED driver output.
5	$\overline{UVLO}$	$V_{CC2}$ undervoltage lockout feedback.
6	$\overline{FAULT}$	DESAT fault feedback.
7	ANODE	Input LED anode.
8	CATHODE	Input LED cathode.
9	$V_{EE2}$	Negative power supply.
10	$V_{CLAMP}$	Miller current clamping output.
11	$V_{OUT}$	Driver output to IGBT gate.
12	$V_{CC2}$	Positive power supply.
13	$V_E$	Common (IGBT emitter) output supply voltage.
14	DESAT	Desaturation voltage input. When the voltage on DESAT exceeds an internal reference voltage of 7V while the IGBT is on, $V_{OUT}$ will soft shut down and $\overline{FAULT}$ will change from high impedance to low logic state.
15	$V_{LED}$	No connection, for testing only.
16	$V_{EE2}$	Negative power supply.

# Ordering Information

ACPL-337J is UL recognized with 5000 V<sub>RMS</sub> for 1 minute per UL1577.

Part Number	Option (RoHS Compliant)	Package	Surface Mount	Tape and Reel	IEC/EN/DIN EN 60747-5-5	Quantity
ACPL-337J	-000E	SO-16	X		X	45 per tube
	-500E		X	X	X	850 per reel

To order, choose a part number from the part number column and combine with the desired option from the option column to form an order entry.

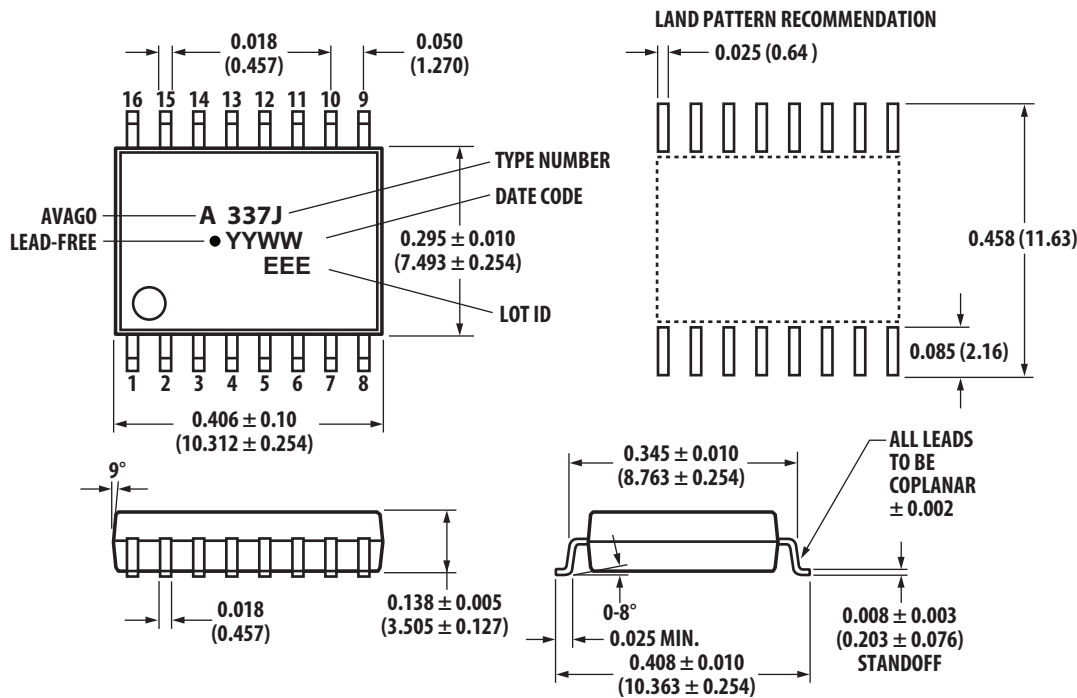
### Example 1:

ACPL-337J-500E to order product of SO-16 surface-mount package in tape and reel packaging with IEC/EN/DIN EN 60747-5-5 safety approval in RoHS compliant.

Option data sheets are available. Contact your Broadcom sales representative or authorized distributor for information.

# Package Outline Drawing

## ACPL-337J 16-Lead Surface-Mount Package



Dimensions in inches (millimeters)

Notes: Initial and continued variation in the color of the ACPL-337J's white mold compound is normal and does not affect device performance or reliability.

Lead coplanarity = 0.1 mm (0.004 inches)

Floating Lead Protrusion is 0.25 mm (10 mils) max.

## Recommended Pb-Free IR Profile

Recommended reflow condition as per JEDEC Standard, J-STD-020 (latest revision). Non-halide flux should be used.

## Regulatory Information

The ACPL-337J is approved by the following organizations:

IEC/EN/DIN EN 60747-5-5	Maximum working insulation voltage $V_{IORM} = 1414 V_{PEAK}$ .
UL	Approval under UL 1577, component recognition program up to $V_{ISO} = 5000 V_{RMS}$ . File E55361.
CSA	Approval under CSA Component Acceptance Notice #5, File CA 88324.

## IEC/EN/DIN EN 60747-5-5 Insulation Characteristics

**NOTE:** Isolation characteristics are guaranteed only within the safety maximum ratings, which must be ensured by protective circuits in application. Surface-mount classification is class A in accordance with CECC 00802.

Description	Symbol	Characteristic	Unit
Installation classification per DIN VDE 0110/39, Table 1 For Rated Mains Voltage $\leq 150 V_{RMS}$ For Rated Mains Voltage $\leq 300 V_{RMS}$ For Rated Mains Voltage $\leq 600 V_{RMS}$ For Rated Mains Voltage $\leq 1000 V_{RMS}$		I – IV I – IV I – IV I – III	
Climatic Classification		40/105/21	
Pollution Degree (DIN VDE 0110/39)		2	
Maximum Working Insulation Voltage	$V_{IORM}$	1414	$V_{PEAK}$
Input to Output Test Voltage, Method b <sup>a</sup> $V_{IORM} \times 1.875 = V_{PR}$ , 100% Production Test with $t_m = 1$ second, Partial Discharge $< 5$ pC	$V_{PR}$	2652	$V_{PEAK}$
Input to Output Test Voltage, Method a <sup>a</sup> $V_{IORM} \times 1.6 = V_{PR}$ , Type and Sample Test, $t_m = 10$ seconds, Partial Discharge $< 5$ pC	$V_{PR}$	2262	$V_{PEAK}$
Highest Allowable Overvoltage (Transient Overvoltage $t_{ini} = 60$ seconds)	$V_{IOTM}$	8000	$V_{PEAK}$
Safety-Limiting Values (Maximum values allowed in the event of a failure) Case Temperature Input Current Output Power	$T_S$ $I_{S,INPUT}$ $P_{S,OUTPUT}$	175 400 1200	$^{\circ}C$ mA mW
Insulation Resistance at $T_S$ , $V_{IO} = 500$ V	$R_S$	$>10^9$	$\Omega$

a. Refer to the optocoupler section of the Isolation and Control Components Designer's Catalog, under Product Safety Regulations section IEC/EN/DIN EN 60747-5-5, for a detailed description of Method a and Method b partial discharge test profiles

## Insulation and Safety Related Specifications

Parameter	Symbol	ACPL-337J	Unit	Conditions
Minimum External Air Gap (Clearance)	L(101)	8.3	mm	Measured from input terminals to output terminals, shortest distance through air.
Minimum External Tracking (Creepage)	L(102)	8.3	mm	Measured from input terminals to output terminals, shortest distance path along body.
Minimum Internal Plastic Gap (Internal Clearance)		0.5	mm	Through insulation distance conductor to conductor, usually the straight line distance thickness between the emitter and detector.
Tracking Resistance (Comparative Tracking Index)	CTI	>175	V	DIN IEC 112/VDE 0303 Part 1.
Isolation Group		IIIa		Material Group (DIN VDE 0110, 1/89, Table 1).

## Absolute Maximum Ratings

Parameter	Symbol	Min.	Max.	Unit	Note
Storage Temperature	$T_S$	-55	125	°C	
Operating Temperature	$T_A$	-40	105	°C	
Output IC Junction Temperature	$T_J$	—	125	°C	
Average Input Current	$I_{F(AVG)}$	—	20	mA	a
Peak Transient Input Current (<1 $\mu$ s pulse width, 300 pps)	$I_{F(TRAN)}$	—	1	A	
Reverse Input Voltage	$V_R$	—	5	V	
Peak Output Current	$ I_{O(PEAK)} $	—	4	A	b
FAULT Output Current	$I_{FAULT}$	—	10	mA	
FAULT Pin Voltage	$V_{FAULT}$	-0.5	$V_{CC1}$	V	
UVLO Output Current	$I_{UVLO}$	—	10	mA	
UVLO Pin Voltage	$V_{UVLO}$	-0.5	$V_{CC1}$	V	
Noninverting Voltage Control Input Voltage	$V_{IN+}$	-0.5	$V_{CC1}$	V	
Integrated LED Driver Output Current	$I_{LEDDRV}$	—	20	mA	
Integrated LED Driver Output Voltage	$V_{LEDDRV}$	-0.5	$V_{CC1}$	V	
Positive Input Supply Voltage	$V_{CC1}$	-0.5	7.0	V	
Total Output Supply Voltage	$V_{CC2} - V_{EE2}$	-0.5	35	V	
Negative Output Supply Voltage	$V_E - V_{EE2}$	-0.5	15	V	c
Positive Output Supply Voltage	$V_{CC2} - V_E$	-0.5	$35 - (V_E - V_{EE})$	V	
Gate Drive Output Voltage	$V_{O(PEAK)}$	-0.5	$V_{CC2}$	V	
Peak Clamping Sinking Current	$I_{CLAMP}$	—	3	A	b
Miller Clamping Pin Voltage	$V_{CLAMP}$	-0.5	$V_{CC2}$	V	
DESAT Voltage	$V_{DESAT}$	$V_E - 0.5$	$(V_{CC2} + 0.5)$	V	
Output IC Power Dissipation	$P_O$	—	600	mW	d
Input LED Power Dissipation	$P_I$	—	150	mW	e

a. Derate linearly above 70°C free-air temperature at a rate of 0.3 mA/°C.

b. Maximum pulse width = 10  $\mu$ s.

c. This supply is optional and is required only when negative gate drive is implemented.

d. Derate linearly above 95°C free-air temperature at a rate of 20 mW/°C.

e. Derate linearly above 95°C free-air temperature at a rate of 5 mW/°C. The maximum LED junction temperature should not exceed 125°C.

## Recommended Operating Conditions

Parameter	Symbol	Min.	Max.	Unit	Note
Operating Temperature	$T_A$	-40	105	°C	
Input Supply Voltage	$V_{CC1}$	4.5	5.5	V	a
Total Output Supply Voltage	$V_{CC2} - V_{EE2}$	15	30	V	b
Negative Output Supply Voltage	$(V_E - V_{EE})$	0	13.5	V	c
Positive Output Supply Voltage	$V_{CC2} - V_E$	15	$30 - (V_E - V_{EE})$	V	
Input LED Current	$I_{F(ON)}$	9	16	mA	
Input Voltage (OFF)	$V_{F(OFF)}$	-3.6	0.8	V	

- In most applications,  $V_{CC1}$  will be powered up first (before  $V_{CC2}$ ) and powered down last (after  $V_{CC2}$ ). This is desirable for maintaining control of the IGBT gate. In applications where  $V_{CC2}$  is powered up first, it is important to ensure that input remains low until  $V_{CC1}$  reaches the proper operating voltage (minimum 4.5V) to avoid any momentary instability at the output during  $V_{CC1}$  ramp-up or ramp-down.
- 15V is the recommended minimum operating positive supply voltage ( $V_{CC2} - V_E$ ) to ensure adequate margin in excess of the maximum  $V_{UVLO+}$  threshold of 13.7V.
- This supply is optional and is required only when negative gate drive is implemented.

## Electrical Specifications (DC)

Unless otherwise noted, all typical values at  $T_A = 25^\circ\text{C}$ ,  $V_{CC1} = 5\text{V}$ ,  $V_{CC2} - V_{EE2} = 30\text{V}$ ,  $V_E - V_{EE2} = 0\text{V}$ . All minimum and maximum specifications are at recommended operating conditions.

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions	Fig.	Note
Logic Low Input Voltage	$V_{IN+L}$	—	—	0.8	V		25	
Logic High Input Voltage	$V_{IN+H}$	2	—	—	V		25	
Logic High LED Driver Output $R_{DS(ON)}$	$R_{LEDDRVH}$	5.5	13.5	24	$\Omega$	$I_{LEDDRV} = -10\text{ mA}$ , $V_{IN+} = 5\text{V}$	25	
Logic Low LED Driver Output Voltage	$V_{LEDDRVL}$	0.2	0.4	0.8	V	$I_{LEDDRV} = 2.4\text{ mA}$ , $V_{IN+} = 0\text{V}$	25	
Input Low Supply Current	$I_{CC1L}$	—	3	6	mA	$I_F = 0\text{ mA}$ , $V_{IN+} = 0\text{V}$	1	
Input High Supply Current	$I_{CC1H}$	—	3	6	mA	$I_F = 10\text{ mA}$ , $V_{IN+} = 0\text{V}$	1	
		—	13	16	mA	$I_{LEDDRV} = 10\text{ mA}$ , $V_{IN+} = 5\text{V}$		
Output Low Supply Current	$I_{CC2L}$	—	4.3	6.5	mA	$I_F = 0\text{ mA}$	2, 3	
Output High Supply Current	$I_{CC2H}$	—	5.4	7.5	mA	$I_F = 10\text{ mA}$	2, 3	
LED Forward Voltage	$V_F$	1.2	1.55	1.95	V	$I_F = 10\text{ mA}$	4	
Temperature Coefficient of Input Forward Voltage	$\Delta V_F / \Delta T_A$	—	-1.7	—	mV/°C	$I_F = 10\text{ mA}$		
LED Reverse Breakdown Voltage	$V_{BR}$	5	—	—	V	$I_F = 10\text{ }\mu\text{A}$		
Input Capacitance	$C_{IN}$	—	70	—	pF			
LED Turn on Current Threshold Low to High	$I_{TH+}$	0.25	2	6	mA	$V_{OUT} = 5\text{V}$		
LED Turn on Current Threshold High to Low	$I_{TH-}$	0.15	1.5	5.5	mA	$V_{OUT} = 5\text{V}$		
LED Turn on Current Hysteresis	$I_{TH\_HYS}$	—	0.5	—	mA			
High Level Output Current	$I_{OH}$	-3	-4.0	—	A	$V_{CC2} - V_{OUT} = 15\text{V}$	5	a
Low Level Output Current	$I_{OL}$	3	3.5	—	A	$V_{OUT} - V_{EE} = 15\text{V}$	6	a

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions	Fig.	Note
High Output Transistor $R_{DS(ON)}$	$R_{DS,OH}$	0.5	2.3	4.5	$\Omega$	$I_{OH} = -3A$	5	b
Low Output Transistor $R_{DS(ON)}$	$R_{DS,OL}$	0.2	1.4	3.6	$\Omega$	$I_{OL} = 3A$	6	b
Low Level Output Current During Fault Condition	$I_{OLF}$	55	115	170	mA	$V_{OUT} - V_{EE} = 14V$	9	c
High Level Output Voltage	$V_{OH}$	$V_{CC2} - 0.5$	$V_{CC2} - 0.15$	—	V	$I_{OUT} = -100\text{ mA}$	7	d, e, f
Low Level Output Voltage	$V_{OL}$	—	0.1	0.5	V	$I_{OUT} = 100\text{ mA}$	8	
Clamp Threshold Voltage	$V_{TH\_CLAMP}$	—	2	3	V			
Clamp Low Level Sinking Current	$I_{CLAMP}$	0.75	1.9	—	A	$V_{CLAMP} = V_{EE} + 2.5$		
Clamp Output Transistor $R_{DS(ON)}$	$R_{DS,CLAMP}$	—	1.1	3.5	$\Omega$	$I_{CLAMP} = 1A$		
$V_{CC2}$ UVLO Threshold Low to High	$V_{UVLO+}$	11	12.5	13.7	V	$V_{OUT} > 5V$		d, f, g
$V_{CC2}$ UVLO Threshold High to Low	$V_{UVLO-}$	10.1	11.3	12.8	V	$V_{OUT} < 5V$		d, f, h
$V_{CC2}$ UVLO Hysteresis	$V_{UVLO\_HYS}$	0.4	1.2	—	V			
DESAT Detection Threshold	$V_{DESAT}$	6.2	7	7.8	V		10	f
DESAT Charging Current	$I_{CHG}$	0.6	1.0	1.2	mA	$V_{DESAT} = 2V$	11	f, i
DESAT Discharging Current	$I_{DSCHG}$	20	58	—	mA	$V_{DESAT} = 8V$	12	
FAULT Logic Low Output Current	$I_{FAULT\_L}$	4	9.0	—	mA	$V_{FAULT} = 0.4V$		
FAULT Logic Low Output Transistor $R_{DS(ON)}$	$R_{DS,FAULT\_L}$	26	44	100	$\Omega$	$V_{FAULT} = 0.4V$		
FAULT Logic High Output Current	$I_{FAULT\_H}$	—	—	20	$\mu A$	$V_{FAULT} = 5V$		
UVLO Logic Low Output Current	$I_{UVLO\_L}$	4	9.0	—	mA	$V_{UVLO} = 0.4V$		
UVLO Logic High Output Current	$I_{UVLO\_H}$	—	—	20	$\mu A$	$V_{UVLO} = 5V$		

- Maximum pulse width = 10  $\mu s$ .
- Output is sourced at  $-3.0A/3.0A$  with a maximum pulse width = 10  $\mu s$ .
- For further details, see the [Description of Operation during DESAT Fault Condition](#) section.
- 15V is the recommended minimum operating positive supply voltage ( $V_{CC2} - V_E$ ) to ensure adequate margin in excess of the maximum  $V_{UVLO+}$  threshold of 13.7V. For High Level Output Voltage testing,  $V_{OH}$  is measured with a DC load current. When driving capacitive loads,  $V_{OH}$  will approach  $V_{CC}$  as  $I_{OH}$  approaches zero.
- Maximum pulse width = 1.0 ms.
- Once  $V_{OUT}$  of ACPL-337J is allowed to go high ( $V_{CC2} - V_E > V_{UVLO+}$ ), the DESAT detection feature of the ACPL-337J will be the primary source of IGBT protection. UVLO is needed to ensure DESAT is functional. Once  $V_{CC2}$  exceeds  $V_{UVLO+}$  threshold, DESAT will remain functional until  $V_{CC2}$  is below  $V_{UVLO-}$  threshold. Thus, the DESAT detection and UVLO features of the ACPL-337J work in conjunction to ensure constant IGBT protection.
- This is the *increasing* (that is, turn-on or *positive-going* direction) of  $V_{CC2} - V_E$ .
- This is the *decreasing* (that is, turn-on or *negative-going* direction) of  $V_{CC2} - V_E$ .
- For further details, see the [DESAT Fault Detection Blanking Time](#) section.

## Switching Specifications (AC)

Unless otherwise noted, all typical values at  $T_A = 25^\circ\text{C}$ ,  $V_{CC1} = 5\text{V}$ ,  $V_{CC2} - V_{EE2} = 30\text{V}$ ,  $V_E - V_{EE2} = 0\text{V}$ . All minimum and maximum specifications are at recommended operating conditions.

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions	Fig.	Note
Input LED to High Level Output Propagation Delay Time	$t_{PLH}$	50	130	220	ns	$R_G = 10\Omega$ , $C_G = 10\text{ nF}$ , $f = 10\text{ kHz}$ , Duty Cycle = 50%	13, 14,15	a
Input LED to Low Level Output Propagation Delay Time	$t_{PHL}$	50	155	250	ns		13, 14,15	b
Pulse Width Distortion	PWD	—	25	120	ns			c, d
Propagation Delay Difference Between Any Two Parts ( $t_{PHL} - t_{PLH}$ )	$P_{DD}$	-150	—	150	ns	d		d, e
Propagation Delay Skew	$t_{PSK}$	—	—	100	ns			d, f
10% to 90% Rise Time	$t_R$	—	80	—	ns			
90% to 10% Fall Time	$t_F$	—	45	—	ns			
DESAT Blanking Time	$t_{DESAT(BLANKING)}$	—	0.6	1.1	$\mu\text{s}$		26	g
DESAT Sense to 90% $V_{OUT}$ Delay	$t_{DESAT(90\%)}$	—	1.3	2	$\mu\text{s}$	$R_G = 10\Omega$ , $C_G = 10\text{ nF}$	26	h
DESAT Sense to 10% $V_{OUT}$ Delay	$t_{DESAT(10\%)}$	—	4.8	6.5	$\mu\text{s}$		26	i
DESAT Sense to DESAT Low Propagation Delay	$t_{DESAT(LOW)}$	—	0.25	—	$\mu\text{s}$		26	j
DESAT Sense to Low Level FAULT Signal Delay	$t_{DESAT(FAULT)}$	—	2.2	5	$\mu\text{s}$	$R_F = 10\text{ k}\Omega$ , $C_F = \text{Open}$	26	k
Output Mute Time due to DESAT	$t_{DESAT(MUTE)}$	2.3	3.0	4.2	ms		26	l
Time Input Kept Low Before Fault Reset to High	$t_{DESAT(RESET)}$	2.3	3.0	4.2	ms	$R_F = 10\text{ k}\Omega$ , $C_F = \text{Open}$	26	m
$V_{CC2}$ to UVLO High Delay	$t_{PLH\_UVLO}$	—	10	—	$\mu\text{s}$		24	n
$V_{CC2}$ to UVLO Low Delay	$t_{PHL\_UVLO}$	—	10	—	$\mu\text{s}$		24	o
$V_{CC2}$ UVLO to $V_{OUT}$ High Delay	$t_{UVLO\_ON}$	—	5.3	—	$\mu\text{s}$		24	p
$V_{CC2}$ UVLO to $V_{OUT}$ Low Delay	$t_{UVLO\_OFF}$	—	1	—	$\mu\text{s}$		24	q
Output High Level Common Mode Transient Immunity	$ CM_H $	30	>50	—	kV/ $\mu\text{s}$	$T_A = 25^\circ\text{C}$ , $I_F = 10\text{ mA}$ , $V_{CM} = 1500\text{V}$ , $V_{CC2} = 30\text{V}$	16, 18,20	r, s
Output Low Level Common Mode Transient Immunity	$ CM_L $	30	>50	—	kV/ $\mu\text{s}$	$T_A = 25^\circ\text{C}$ , $I_F = 0\text{ mA}$ , $V_{CM} = 1500\text{V}$ , $V_{CC2} = 30\text{V}$	17, 19,21	t, s

- $t_{PLH}$  is defined as propagation delay from 50% of LED input  $I_F$  to 50% of high level output.
- $t_{PHL}$  is defined as propagation delay from 50% of LED input  $I_F$  to 50% of low level output.
- Pulse Width Distortion (PWD) is defined as  $|t_{PHL} - t_{PLH}|$  for any given unit.
- As measured from  $I_F$  to  $V_{OUT}$ .
- The difference between  $t_{PHL}$  and  $t_{PLH}$  between any two ACPL-337J parts under the same test conditions.
- $t_{PSK}$  is equal to the worst-case difference in  $t_{PHL}$  and  $t_{PLH}$  that will be seen between units under the same test conditions.
- The ACPL-337J internal delay time to respond to a DESAT fault condition without any external DESAT capacitor.
- The amount of time from when DESAT threshold is exceeded to 90% of  $V_{GATE}$  at mentioned test conditions.
- The amount of time from when DESAT threshold is exceeded to 10% of  $V_{GATE}$  at mentioned test conditions.
- The amount of time from when DESAT threshold is exceeded to DESAT low voltage, 0.7V.
- The amount of time from when DESAT threshold is exceeded to FAULT output low – 50% of  $V_{CC1}$  voltage.

- l. The amount of time when DESAT threshold is exceeded, output is muted to LED input.
- m. The amount of time when DESAT mute time is expired, LED input must be kept low for FAULT status to return to high.
- n. The delay time when  $V_{CC2}$  exceeds UVLO+ threshold to UVLO high – 50% of UVLO positive-going edge.
- o. The delay time when  $V_{CC2}$  exceeds UVLO– threshold to UVLO low – 50% of UVLO negative-going edge.
- p. The delay time when  $V_{CC2}$  exceeds UVLO+ threshold to 50% of high level output.
- q. The delay time when  $V_{CC2}$  exceeds UVLO– threshold to 50% of low level output.
- r. Common mode transient immunity in the high state is the maximum tolerable  $dV_{CM}/dt$  of the common mode pulse,  $V_{CM}$ , to ensure that the output will remain in the high state (that is,  $V_{OUT} > 15V$  or  $FAULT > 2V$  or  $UVLO > 2V$ ). A 330 pF and a 10 k $\Omega$  pull-up resistor are needed in FAULT and UVLO detection mode.
- s. Split resistor network in the ratio 1:1 at the anode and cathode. For further details, see [Description of Input LED Driver and Split Resistors Circuit](#).
- t. Common mode transient immunity in the low state is the maximum tolerable  $dV_{CM}/dt$  of the common mode pulse,  $V_{CM}$ , to ensure that the output will remain in a low state (that is,  $V_{OUT} < 1.0V$  or  $FAULT < 0.8V$  or  $UVLO < 0.8V$ ).

## Package Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions	Note
Input-Output Momentary Withstand Voltage	$V_{ISO}$	5000	—	—	$V_{RMS}$	RH < 50%, t = 1 min., $T_A = 25^\circ C$	a, b, c
Resistance (Input-Output)	$R_{I-O}$	—	> $10^9$	—	$\Omega$	$V_{I-O} = 500 V_{DC}$	c
Capacitance (Input-Output)	$C_{I-O}$	—	1.3	—	pF	Freq = 1 MHz	
Thermal Coefficient Between							d
LED and Input IC	$A_{EI}$		35.4		$^\circ C/W$		
LED and Output IC	$A_{EO}$		33.1		$^\circ C/W$		
Input IC and Output IC	$A_{IO}$		25.6		$^\circ C/W$		
LED and Ambient	$A_{EA}$		176.1		$^\circ C/W$		
Input IC and Ambient	$A_{IA}$		92		$^\circ C/W$		
Output IC and Ambient	$A_{OA}$		76.7		$^\circ C/W$		

- a. In accordance with UL1577, each optocoupler is proof tested by applying an insulation test voltage  $\geq 6000 V_{RMS}$  for 1 second. This test is performed before the 100% production test for partial discharge (method b) shown in the [IEC/EN/DIN EN 60747-5-5 Insulation Characteristics](#) table, if applicable.
- b. The input-output momentary withstand voltage is a dielectric voltage rating that should not be interpreted as an input-output continuous voltage rating. For the continuous voltage rating, refer to your equipment level safety specification or the [IEC/EN/DIN EN 60747-5-5 Insulation Characteristics](#) table.
- c. The device considered a two-terminal device: pins 1 to 8 are shorted together and pins 9 to 16 are shorted together
- d. For further details, see [Thermal Calculation](#) section.

Figure 1:  $I_{CC1}$  vs. Temperature

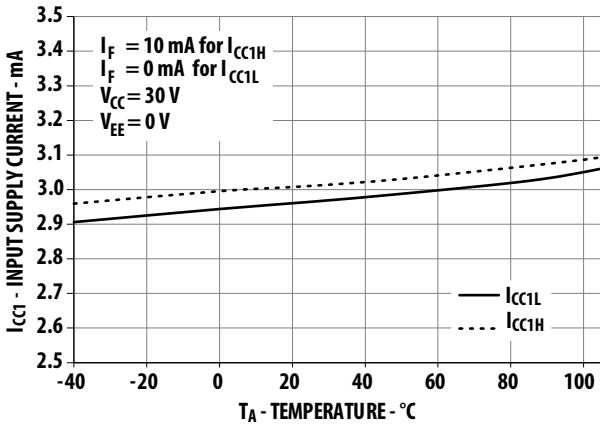


Figure 2:  $I_{CC2}$  vs. Temperature

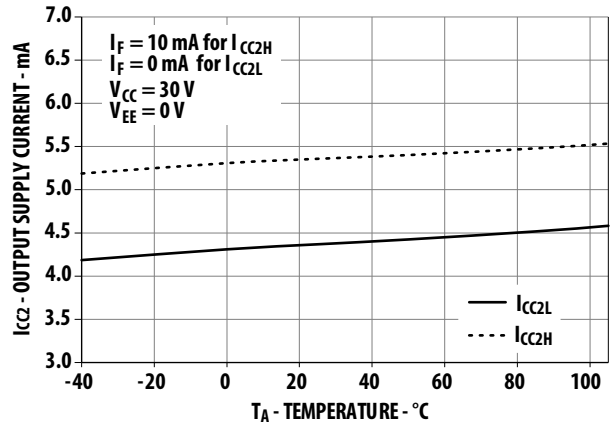


Figure 3:  $I_{CC}$  vs.  $V_{CC}$

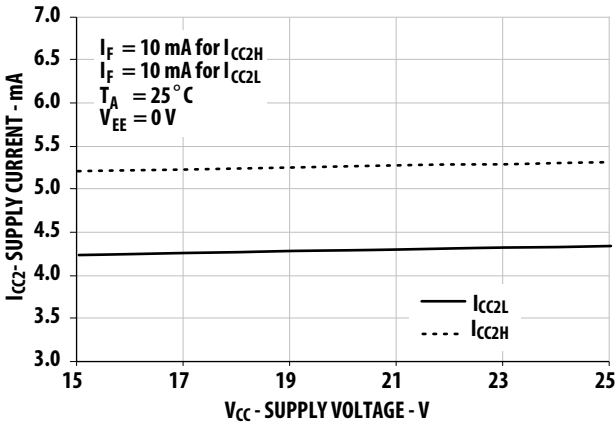


Figure 4: LED1 Input Current vs. Forward Voltage

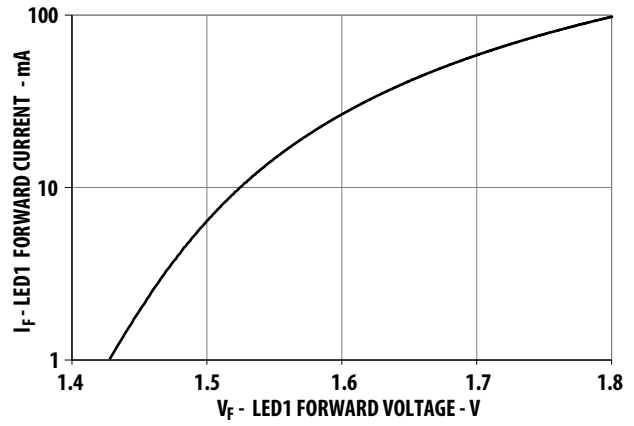


Figure 5:  $I_{OH}$  vs.  $V_{OH}$

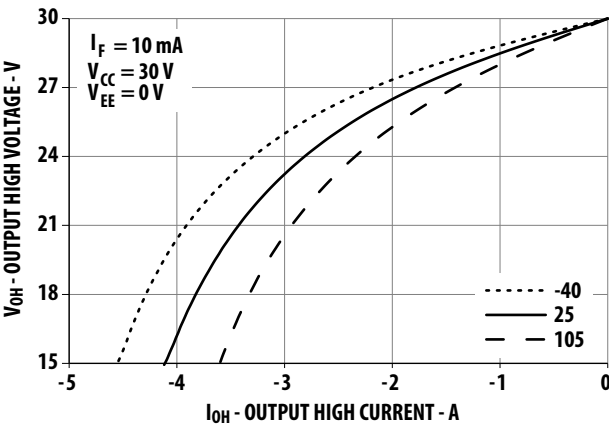


Figure 6:  $I_{OL}$  vs.  $V_{OL}$

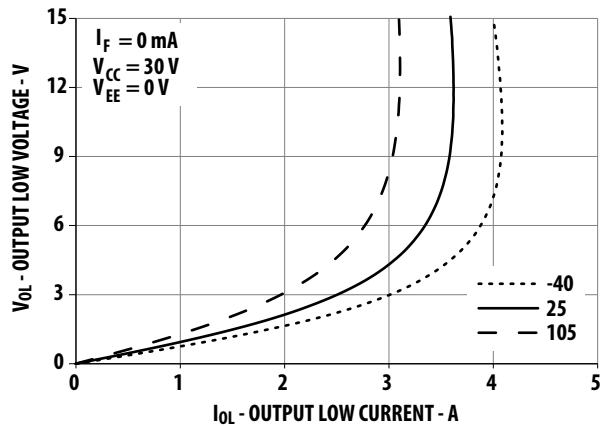


Figure 7:  $V_{OH}$  vs. Temperature

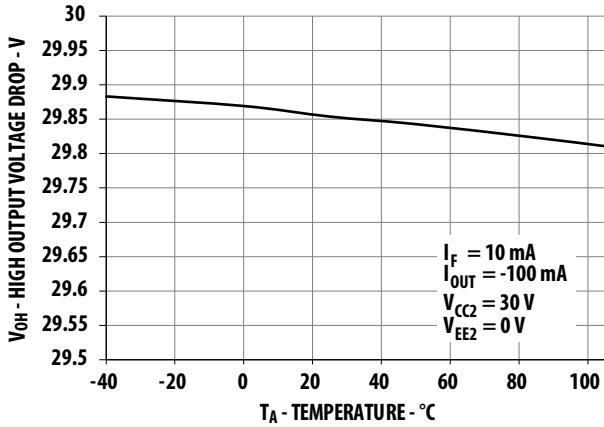


Figure 8:  $V_{OL}$  vs. Temperature

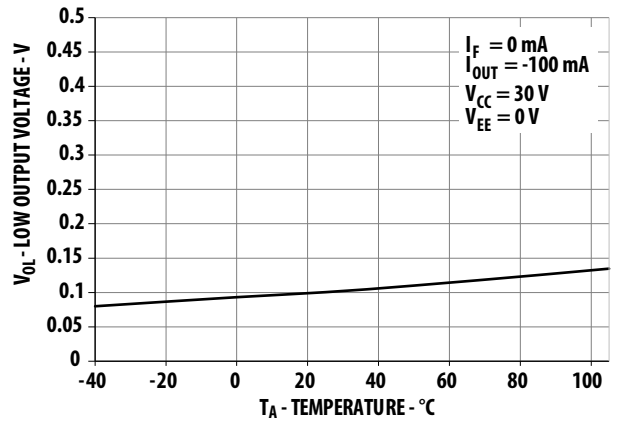


Figure 9:  $I_{OLF}$  vs. Output Voltage

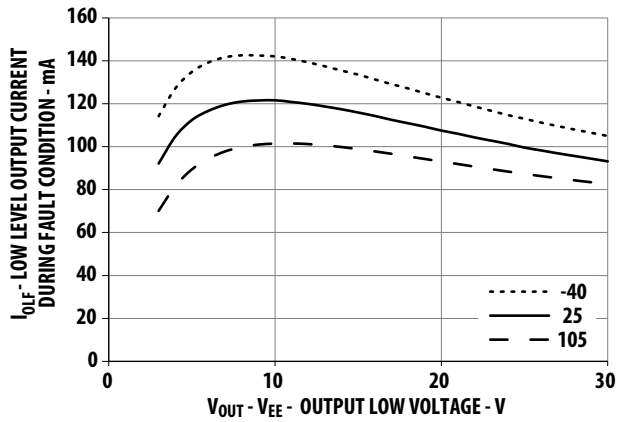


Figure 10:  $V_{DESAT}$  vs. Temperature

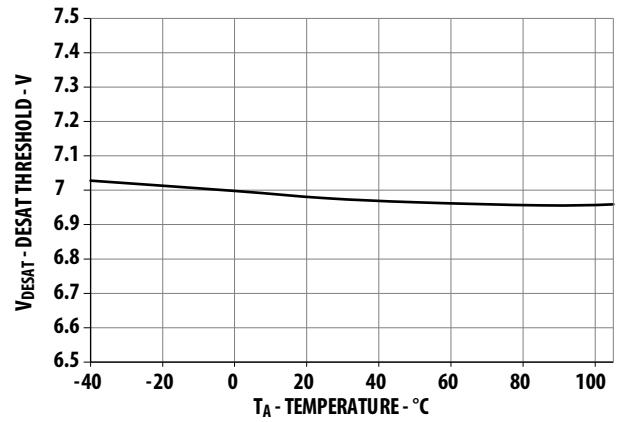


Figure 11:  $I_{CHG}$  vs. Temperature

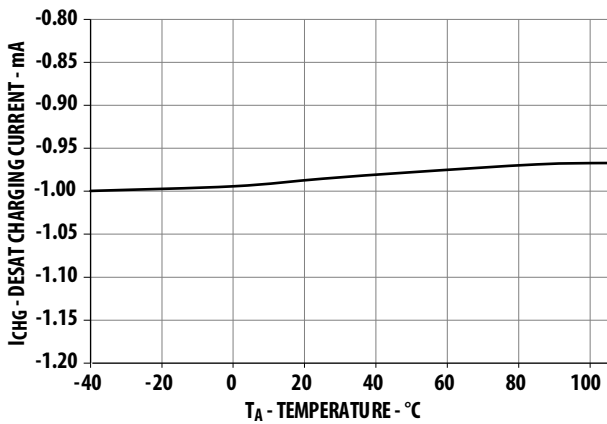


Figure 12:  $I_{DSCHG}$  vs. Temperature

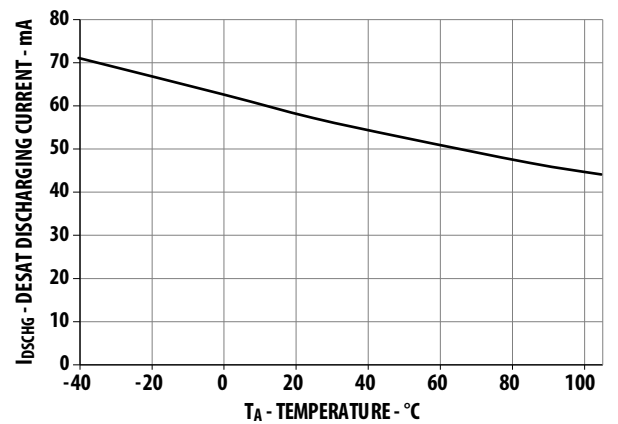


Figure 13: Propagation Delay vs. Temperature

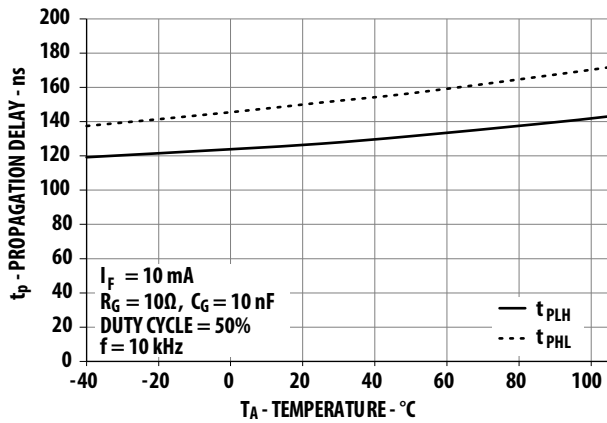


Figure 14: Propagation Delay vs. Supply Voltage

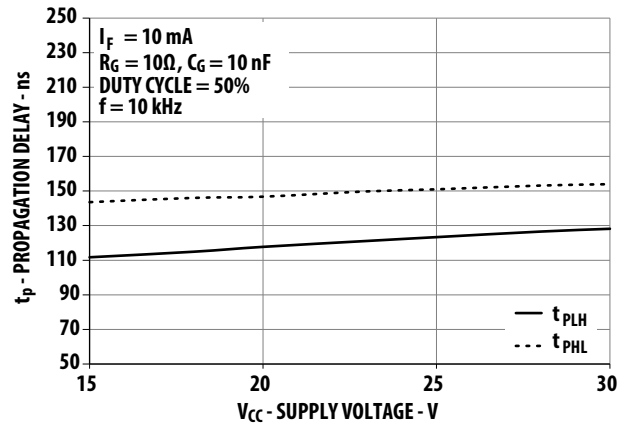


Figure 15: Propagation Delay vs. Load Resistance

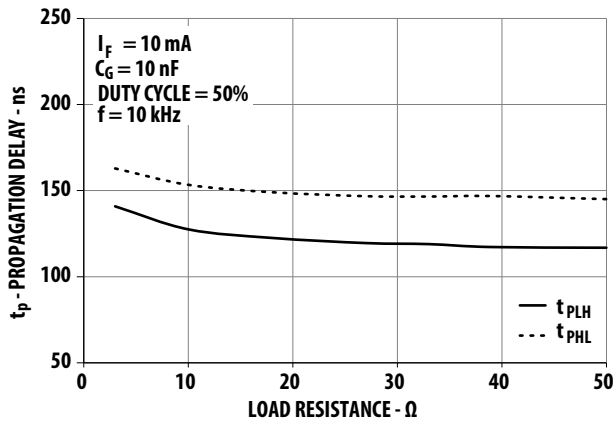


Figure 16: CMR  $V_{OUT}$  High Test Circuit

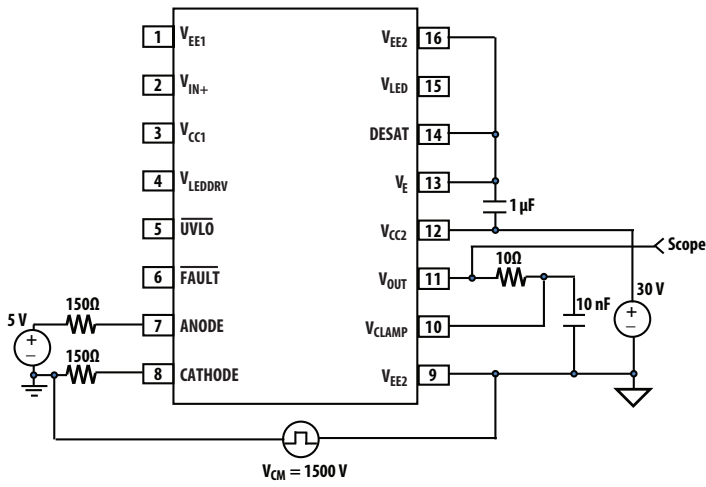


Figure 17: CMR  $V_{OUT}$  Low Test Circuit

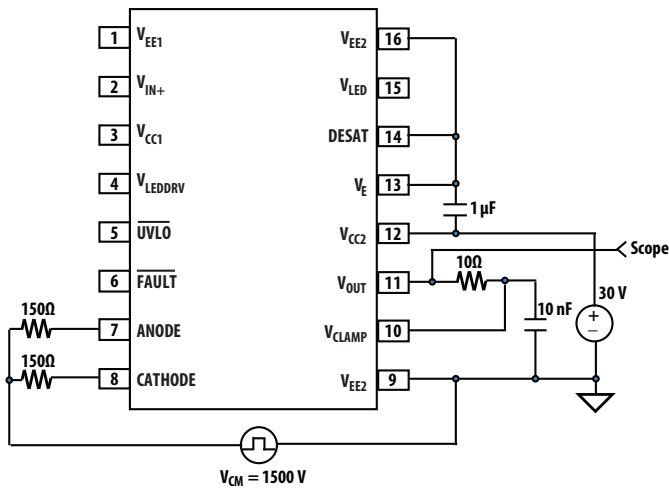


Figure 18: CMR FAULT High Test Circuit

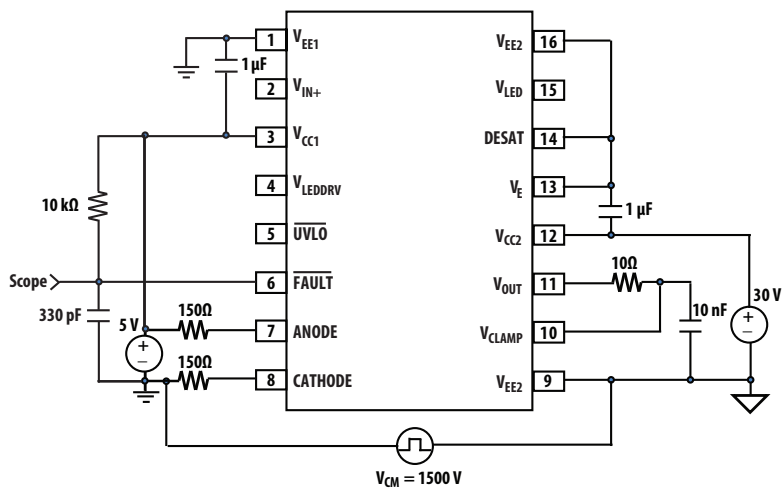


Figure 19: CMR FAULT Low Test Circuit

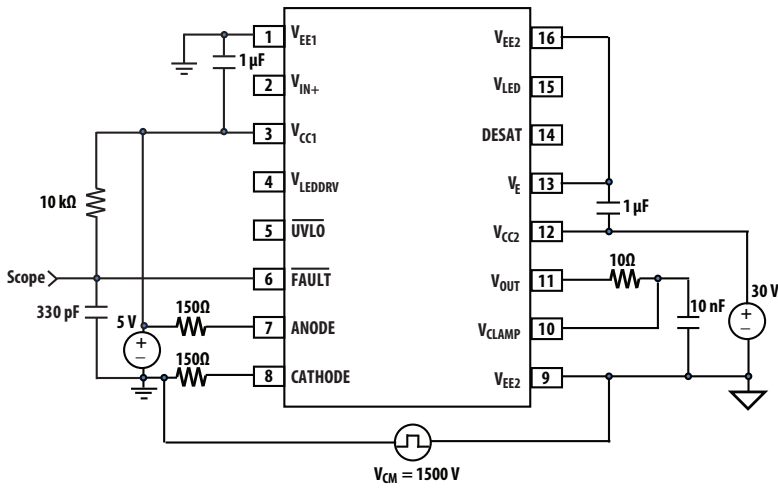


Figure 20: CMR UVLO High Test Circuit

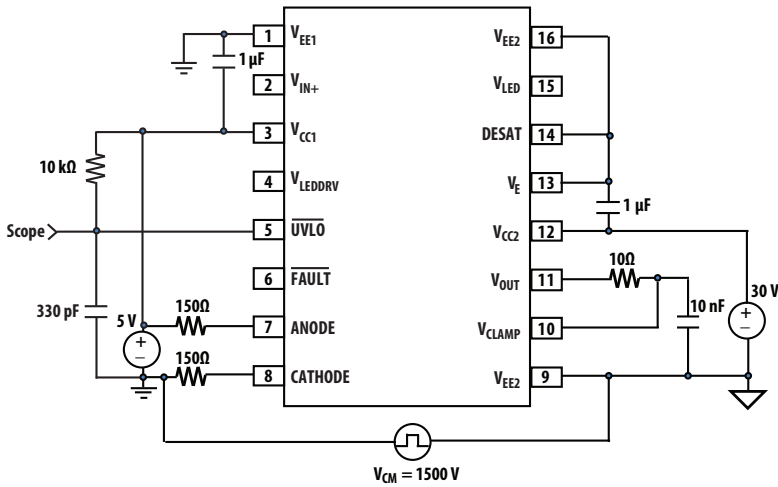
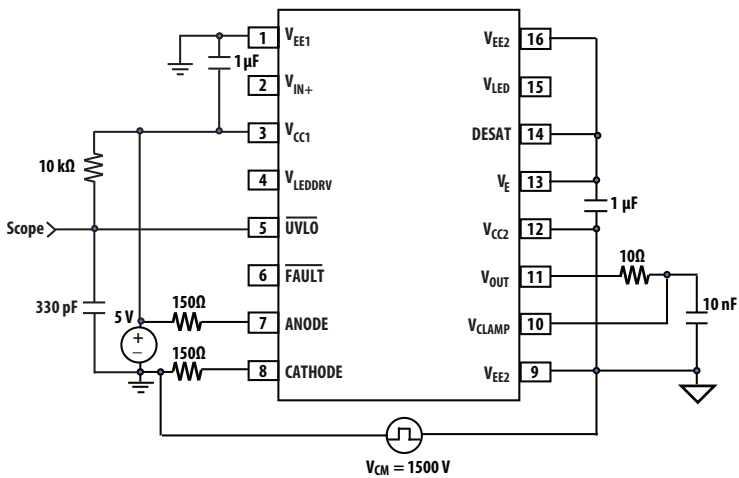


Figure 21: CMR UVLO Low Test Circuit



# Application Information

## Recommended Application Circuit

Figure 22: Typical Gate Drive Circuits with DESAT Detection

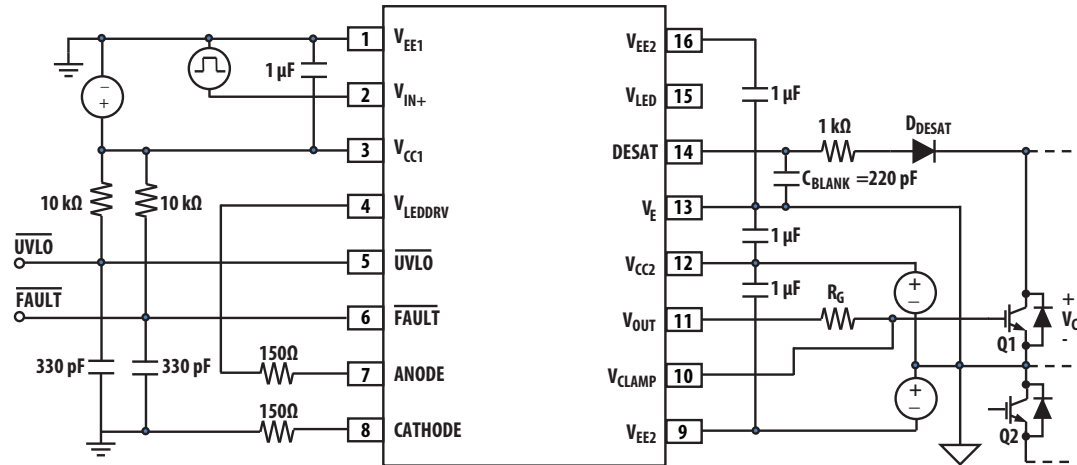
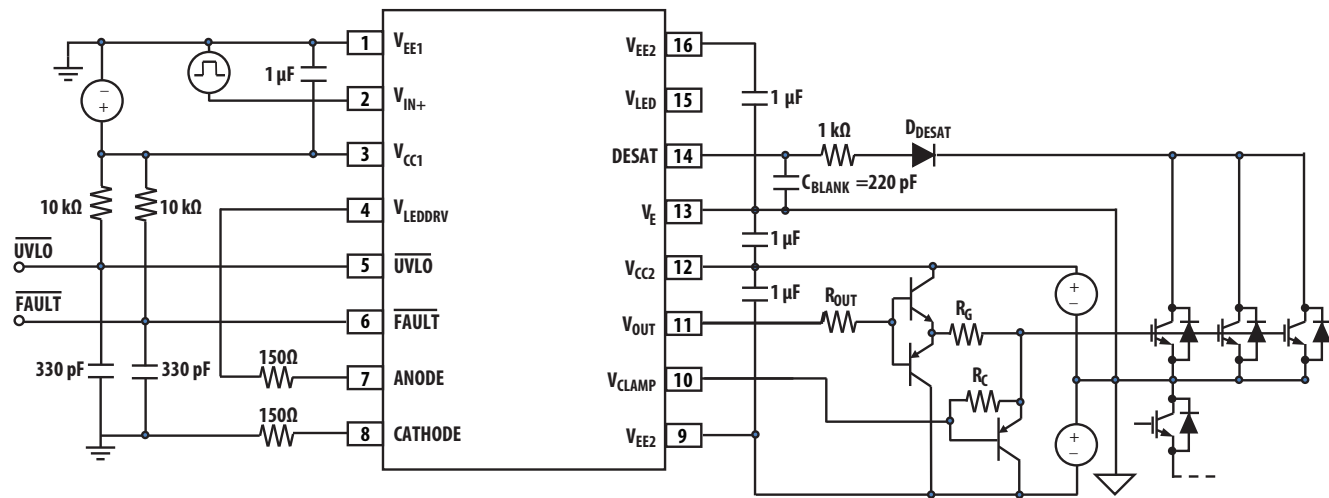


Figure 23: Typical Parallel IGBT Gate Drive Circuits with DESAT Detection



The ACPL-337J has noninverting gate control inputs, and an open-drain FAULT and UVLO outputs suitable for wired OR applications. The two supplies bypass capacitors (1  $\mu$ F) provide the large transient currents necessary during a switching transition. The DESAT diode and 220-pF blanking capacitor are the necessary external components for the fault detection circuitry. The gate resistor ( $R_G$ ) serves to limit gate charge current and indirectly control the IGBT collector voltage rise and fall times. The open-drain FAULT and UVLO outputs have passive 10-k $\Omega$  pull-up resistors and a 330-pF filtering capacitor.

## Introduction to DESAT Detection

The power stage of a typical three-phase inverter is susceptible to several types of failures, most of which are potentially destructive to the power IGBTs. These failure modes can be grouped into four basic categories: phase and/or rail supply short circuits due to user misconnect or bad wiring, control signal failures due to noise or computational errors, overload conditions induced by the load, and component failures in the gate drive circuitry. Under any of these fault conditions, the current through the IGBTs can increase rapidly, causing excessive power dissipation and heating. The IGBTs become damaged when the current load approaches the saturation current of the device, and the collector to emitter voltage rises above the saturation voltage level. The drastically increased power dissipation very quickly overheats the power device and destroys it. To prevent damage to the drive, fault protection must be implemented to reduce or turn-off the IGBTs during a fault condition.

A circuit providing fast local DESAT detection and shutdown is an ideal solution, but the number of required components, board space consumed, cost, and complexity have until now limited its use to high-performance drives. The features that this circuit must have are high speed, low cost, low resolution, low power dissipation, and small size. The ACPL-337J satisfies these criteria by combining a high speed, high output current driver, high voltage optical isolation between the input and output, local IGBT desaturation detection and shut down, and optically isolated fault and UVLO status feedback signal into a single 16-pin surface-mount package.

The fault detection method, which is adopted in the ACPL-337J, is to monitor the saturation (collector) voltage of the IGBT and to trigger a local fault shutdown sequence if the collector voltage exceeds a predetermined threshold. A small gate discharge device slowly reduces the high short circuit IGBT current to prevent damaging voltage spikes. Before the dissipated energy can reach destructive levels, the IGBT is shut off. During the off state of the IGBT, the fault detect circuitry is simply disabled to prevent false *fault* signals.

The alternative protection scheme of measuring IGBT current to prevent desaturation is effective if the short circuit capability of the power device is known, but this method will fail if the gate drive voltage decreases enough to only partially turn on the IGBT. By directly measuring the collector voltage, the ACPL-337J limits the power dissipation in the IGBT even with insufficient gate drive voltage. Another more subtle advantage of the desaturation detection method is that power dissipation in the IGBT is monitored, while the current sense method relies on a preset current threshold to predict the safe limit of operation. Therefore, an overly conservative overcurrent threshold is not needed to protect the IGBT.

## Output Control

The outputs ( $V_{OUT}$ ,  $\overline{FAULT}$ , and  $\overline{UVLO}$ ) of the ACPL-337J are controlled by the combination of  $V_{CC1}$ ,  $V_{CC2}$ (UVLO), LED current  $I_F$  and IGBT desaturation condition. The following table shows the logic truth table for these outputs.

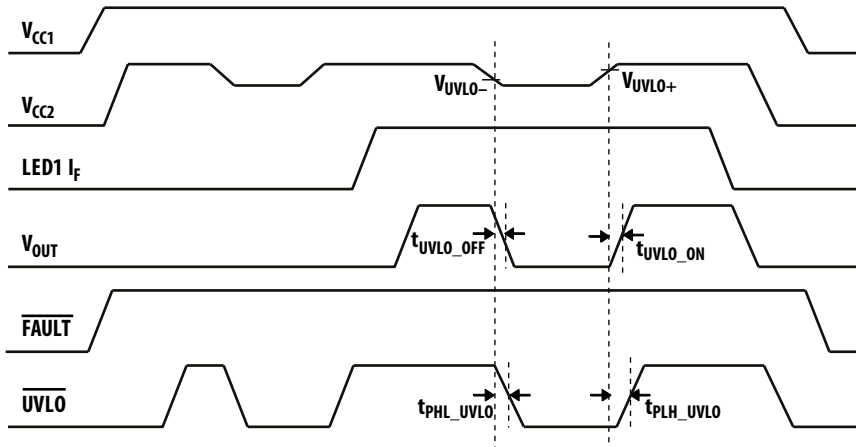
$V_{CC1}$	$V_{CC2}$ (UVLO)	$I_F$	DESAT	$V_{OUT}$	$\overline{FAULT}$	$\overline{UVLO}$
Low	Low	X	Not Active	Low	Low	Low
Low	High	Low	Not Active	Low	Low	Low
Low	High	High	Active (no DESAT fault)	High	Low	Low
Low	High	High	Active (DESAT fault)	Low	Low	Low
High	Low	X	Not Active	Low	High	Low
High	High	High	Active (DESAT fault)	Low	Low	High
High	High	Low	Not Active	Low	High	High
High	High	High	Active (no DESAT fault)	High	High	High

The logic level is defined by the respective threshold of each function pin.

## Description of Undervoltage Lockout

Insufficient gate voltage to IGBT can increase turn-on resistance of IGBT, resulting in large power loss and IGBT damage due to high heat dissipation. ACPL-337J monitors the output power supply constantly. When output power supply is lower than undervoltage lockout (UVLO) threshold, the gate driver output will shut off to protect IGBT from low voltage bias. The low output power supply fault will be reported via the UVLO feedback. In this way, the UVLO feedback can also serve as a READY signal to the controller during power up.

Figure 24: UVLO and Feedback Behaviors and Timing Diagram

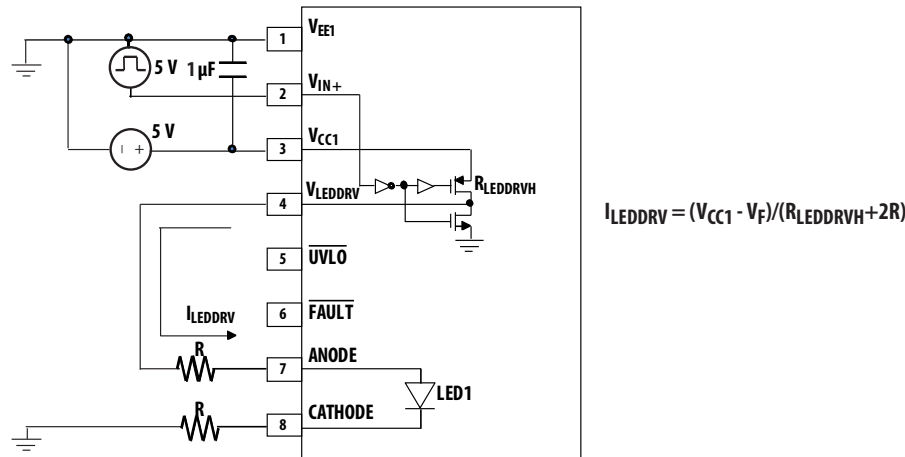


## Description of Input LED Driver and Split Resistors Circuit

The ACPL-337J has integrated an input LED driver that with high impedance input ( $V_{IN+}$ ) for interfacing with the controller. The LED driver's output ( $V_{LEDDRV}$ ) has to be connected with the recommended split resistors circuit to the LED1 anode to achieve the rated high CMR performance. The LED current can be calculated by  $I_{LEDDRV} = (V_{CC1} - V_F) / (R_{LEDDRVH} + 2R)$ . Alternatively, if the LED driver is not used, LED1 can still be driven directly by other means of discrete driver configuration.

It is recommended that the two resistors ( $R$ ) connected to input LED's anode and cathode are split in the ratio 1:1. They will help to balance the common mode impedances at the LED's anode and cathode. This helps to equalize the common mode voltage changes at the anode and cathode to give high CMR performance.

Figure 25: Input LED Driver Functional Diagram



## DESAT Fault Detection Blanking Time

The DESAT fault detection circuitry must remain disabled for a short time period following the turn-on of the IGBT to allow the collector voltage to fall below the DESAT threshold. This time period, called the DESAT blanking time, is controlled by the internal DESAT charge current, the DESAT voltage threshold, and the external DESAT capacitor.

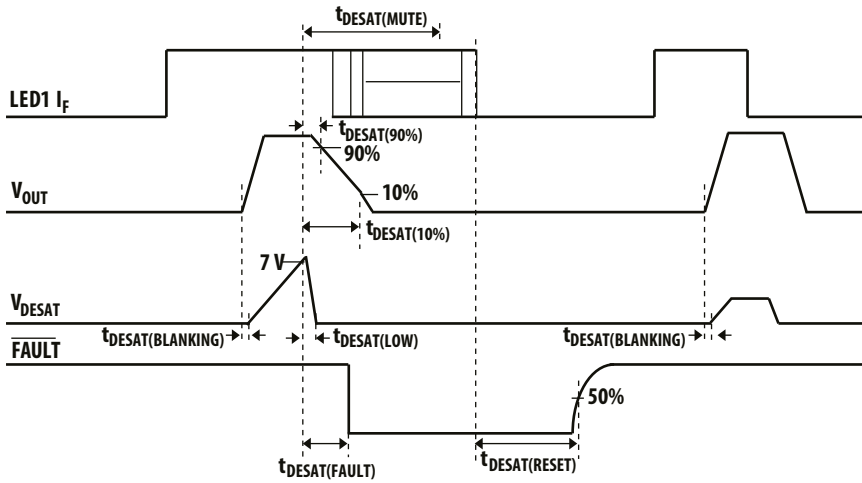
The nominal blanking time is calculated in terms of external capacitance ( $C_{BLANK}$ , see [Figure 22](#) and [Figure 23](#)), FAULT threshold voltage ( $V_{DESAT}$ ), and DESAT charge current ( $I_{CHG}$ ) in addition to an internal DESAT blanking time ( $t_{DESAT(BLANKING)}$ ).

$$t_{BLANK} = C_{BLANK} \times (V_{DESAT} / I_{CHG}) + t_{DESAT(BLANKING)}$$

## Description of Operation during DESAT Fault Condition

1. The DESAT terminal monitors IGBT's  $V_{CE}$  voltage.
2. When the voltage on the DESAT terminal exceeds 7V, a weak pull-down in the output stage ( $I_{OLP}$ ) will turn on to *softly* turn off the IGBT. When the gate voltage falls below  $V_{EE} + 2V$ , the Miller clamp will turn on to clamp the IGBT gate to  $V_{EE}$ .
3. The FAULT output goes low, notifying the microcontroller of the fault condition.
4. The microcontroller takes the appropriate action.
5. When  $t_{DESAT(MUTE)}$  expires, the LED input must be kept low for  $t_{DESAT(RESET)}$  before the fault condition is cleared. FAULT status will return to high.
6. Output ( $V_{OUT}$ ) starts to respond to the LED input after the fault condition is cleared.

Figure 26: DESAT Fault State Timing Diagram



## Selecting the Gate Resistor ( $R_G$ )

**Step 1:** Calculate  $R_G$  minimum from the  $I_{O(PEAK)}$  specification. The IGBT and  $R_G$  in Figure 22 can be analyzed as a simple RC circuit with a voltage supplied by ACPL-337J.

$$R_G \geq \frac{V_{CC} - V_{EE}}{I_{O(PEAK)}} - R_{DS,OH(MIN)} \quad R_G \geq \frac{V_{CC} - V_{EE}}{I_{O(PEAK)}} - R_{DS,OL(MIN)}$$

$$= \frac{30 - 0 \text{ V}}{4 \text{ A}} - 0.5 \Omega \quad \text{or} \quad = \frac{30 - 0 \text{ V}}{4 \text{ A}} - 0.2 \Omega$$

$$= 7 \Omega \quad \quad \quad = 7.3 \Omega$$

The external gate resistor,  $R_G$ , and internal minimum turn-on resistance,  $R_{DS,ON}$  will ensure the output current will not exceed the device absolute maximum rating of 4A. In this case, we will use worst-case  $R_G \geq 7.3 \Omega$ .

**Step 2:** Check the ACPL-337J power dissipation and increase  $R_G$  if necessary. The ACPL-337J total power dissipation ( $P_T$ ) is equal to the sum of the LED power ( $P_E$ ), input IC power ( $P_I$ ), and the output IC power ( $P_O$ ).

$$P_T = P_E + P_I + P_O$$

Assuming operation conditions of  $I_F$  (worst case) = 16 mA,  $R_G = 7.3 \Omega$ , maximum duty cycle = 80%,  $Q_G = 1 \mu\text{C}$ ,  $f = 10 \text{ kHz}$  and  $T_A \text{ max.} = 95^\circ\text{C}$ .

## Calculation of LED Power Dissipation

$$P_E = I_F \times V_F \times \text{Duty Cycle}$$

$$= 16 \text{ mA} \times 1.95 \text{ V} \times 0.8 = 25 \text{ mW}$$

## Calculation of Input IC Power Dissipation

$$P_I = I_{CC1(\text{max.})} \times V_{CC1(\text{Recommended Max.})}$$

$$= 6 \text{ mA} \times 5.5 \text{ V} = 33 \text{ mW}$$

## Calculation of Input IC Power Dissipation

$$P_O = P_{O(\text{BIAS})} + P_{O(\text{SWITCHING})}$$

$$= I_{CC2} \times (V_{CC2} - V_{EE2}) + P_{HS} + P_{LS}$$

$$P_{HS} = (V_{CC2} \times Q_G \times f) \times R_{DS,OH(\text{MAX})} / (R_{DS,OH(\text{MAX})} + R_G) / 2$$

$$P_{LS} = (V_{CC2} \times Q_G \times f) \times R_{DS,OL(\text{MAX})} / (R_{DS,OL(\text{MAX})} + R_G) / 2$$

$$P_{HS} = (30V \times 1 \mu C \times 10 \text{ kHz}) \times 4.5\Omega / (4.5\Omega + 7.3\Omega) / 2 = 57.2 \text{ mW}$$

$$P_{LS} = (30V \times 1 \mu C \times 10 \text{ kHz}) \times 3.6\Omega / (3.6\Omega + 7.3\Omega) / 2 = 49.5 \text{ mW}$$

$$P_O = 7.5 \text{ mA} \times 30V + 57.2 \text{ mW} + 49.5 \text{ mW}$$

$$= 331.7 \text{ mW} < 600 \text{ mW} (P_{O(\text{MAX})} \text{ at } 95^\circ\text{C})$$

The value of 7.5 mA for  $I_{CC2}$  in the previous equation is the maximum  $I_{CC2}$  over the entire operating temperature range.

Because  $P_O$  is less than  $P_{O(\text{MAX})}$ ,  $R_G = 7.3\Omega$  is correct for the power dissipation.

## Thermal Calculation

The application and environmental design for the ACPL-337J must ensure that the junction temperature of the internal ICs and LED within the gate driver optocoupler do not exceed 125°C. The following equations calculate the maximum power dissipation effect on junction temperatures.

LED Junction Temperature:

$$T_E = A_{EA} \times P_E + A_{EI} \times P_I + A_{EO} \times P_O + T_A$$

$$= 176.1^\circ\text{C/W} \times 25 \text{ mW} + 35.4^\circ\text{C/W} \times 33 \text{ mW} + 33.1^\circ\text{C/W} \times 331.7 \text{ mW} + 95^\circ\text{C}$$

$$= 111.5^\circ\text{C}$$

Input IC Junction Temperature:

$$T_I = A_{EI} \times P_E + A_{IA} \times P_I + A_{IO} \times P_O + T_A$$

$$= 35.4^\circ\text{C/W} \times 25 \text{ mW} + 92^\circ\text{C/W} \times 33 \text{ mW} + 25.6 \times 331.7 \text{ mW} + 95^\circ\text{C}$$

$$= 107.4^\circ\text{C}$$

Output IC Junction Temperature:

$$T_O = A_{EO} \times P_E + A_{IO} \times P_I + A_{OA} \times P_O + T_A$$

$$= 33.1^\circ\text{C/W} \times 25 \text{ mW} + 25.6^\circ\text{C/W} \times 33 \text{ mW} + 76.7 \times 331.7 \text{ mW} + 95^\circ\text{C}$$

$$= 122.1^\circ\text{C}$$

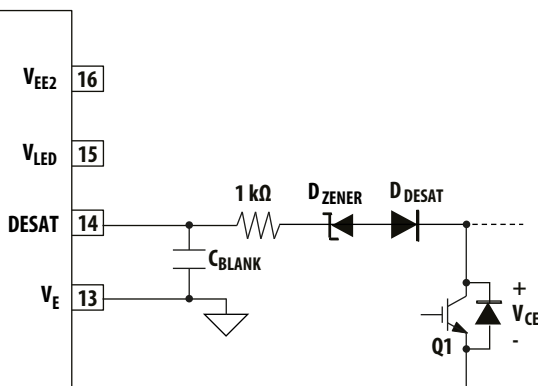
## DESAT Diode and DESAT Threshold

The DESAT diode's function is to conduct forward current, allowing sensing of the IGBT's saturated collector-to-emitter voltage,  $V_{CESAT}$ , (when the IGBT is *on*) and to block high voltages (when the IGBT is *off*).

When the IGBT is switching off and toward the end of the forward conduction of the DESAT diode, a reverse current will flow for short time. This reverse recovery effect prevents the diode from achieving its blocking capability until the mobile charge in the junction is depleted. During this time, there is commonly a very high  $dV_{CE}/dt$  voltage ramp rate across the IGBT's collector-to-emitter. This results in  $I_{CHARGE} = C_{D-DESAT} \times dV_{CE}/dt$  charging current, which will charge the blanking capacitor,  $C_{BLANK}$ . To minimize this charging current and avoid false DESAT triggering, it is best to use fast-response diodes.

In the recommended application circuit shown in [Figure 22](#), the voltage on pin 14 (DESAT) is  $V_{DESAT} = V_F + V_{CE}$ , where  $V_F$  is the forward ON voltage of  $D_{DESAT}$  and  $V_{CE}$  is the IGBT collector-to-emitter voltage. The value of  $V_{CE}$  that triggers DESAT to signal a FAULT condition is nominally  $7V - V_F$ . If desired, this DESAT threshold voltage can be decreased by using multiple DESAT diodes or low-voltage Zener diode in series. If  $n$  is the number of DESAT diodes, the nominal threshold value becomes  $V_{CE,FAULT(TH)} = 7V - n \times V_F$ . If a Zener diode is used, the nominal threshold value becomes  $V_{CE,FAULT(TH)} = 7V - V_F - V_Z$ . When using two diodes instead of one, then diodes with half of the total required maximum reverse-voltage rating may be chosen.

Figure 27: DESAT Diode and DESAT Threshold



## DESAT Pin Protection Resistor

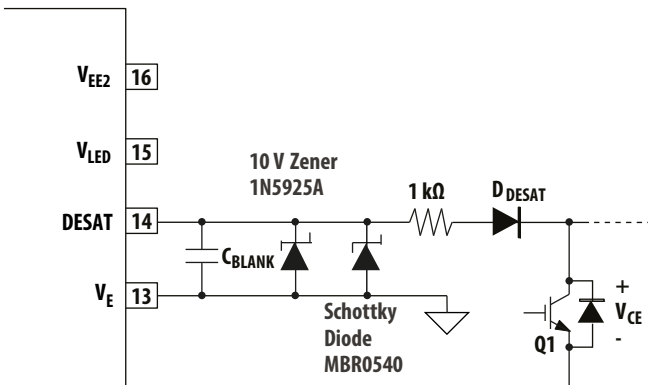
The freewheeling of flyback diodes connected across the IGBTs can have large instantaneous forward voltage transients that greatly exceed the nominal forward voltage of the diode. This may result in a large negative voltage spike on the DESAT pin, which will draw substantial current out of the driver if protection is not used. To limit this current to levels that will not damage the driver IC, make sure a 1-k $\Omega$  resistor is inserted in series with the DESAT diode.

## False Fault Prevention Diodes

A situation that may cause the driver to generate a false fault signal is if the substrate diode of the driver becomes forward biased. This can happen if the reverse recovery spikes coming from the IGBT freewheeling diodes bring the DESAT pin below ground. Therefore, the DESAT pin voltage will be *brought* above the threshold voltage. These negative-going voltage spikes are typically generated by inductive loads or reverse recovery spikes of the IGBT/MOSFETs freewheeling diodes. To prevent a false fault signal, connect a Zener diode and a Schottky diode across the DESAT pin and  $V_E$  pin.

Figure 28 shows this circuit solution. The Schottky diode will prevent the substrate diode of the gate driver optocoupler from being forward biased while the Zener diode (10V) is used to prevent any positive high transient voltage from affecting the DESAT pin.

Figure 28: False Fault Prevention Diodes



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